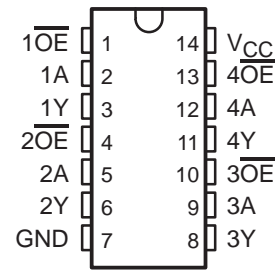


SN74ALVC125 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES110D – JULY 1997 – REVISED DECEMBER 1998

- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

D, DGV, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVC125 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

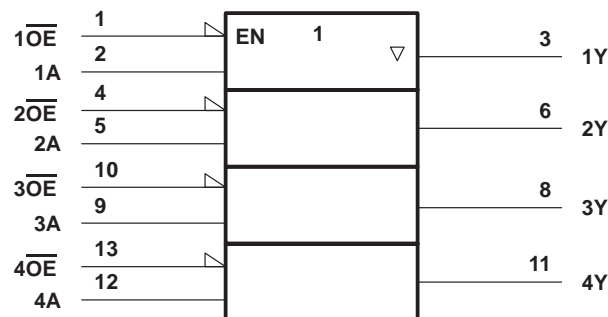
To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC125 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
\overline{OE}	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1998, Texas Instruments Incorporated

SN74ALVC125
QUADRUPLE BUS BUFFER GATE
WITH 3-STATE OUTPUTS

SCES110D – JULY 1997 – REVISED DECEMBER 1998

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	1.65	3.6	V
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	1.7	
		V _{CC} = 2.7 V to 3.6 V	2	
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	0.7	
		V _{CC} = 2.7 V to 3.6 V	0.8	
V _I	Input voltage	0	V _{CC}	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V	-4	mA
		V _{CC} = 2.3 V	-12	
		V _{CC} = 2.7 V	-12	
		V _{CC} = 3 V	-24	
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4	mA
		V _{CC} = 2.3 V	12	
		V _{CC} = 2.7 V	12	
		V _{CC} = 3 V	24	
T _A	Operating free-air temperature	-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

SN74ALVC125
QUADRUPLE BUS BUFFER GATE
WITH 3-STATE OUTPUTS

SCES110D – JULY 1997 – REVISED DECEMBER 1998

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}		I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2			V
		I _{OH} = -4 mA	1.65 V	1.2			
		I _{OH} = -6 mA	2.3 V	2			
		I _{OH} = -12 mA	2.3 V	1.7			
			2.7 V	2.2			
			3 V	2.4			
V _{OL}		I _{OL} = 100 μA	1.65 V to 3.6 V			0.2	V
		I _{OL} = 4 mA	1.65 V			0.45	
		I _{OL} = 6 mA	2.3 V			0.4	
		I _{OL} = 12 mA	2.3 V			0.7	
			2.7 V			0.4	
			3 V			0.55	
I _I		V _I = V _{CC} or GND	3.6 V			±5	μA
I _{OZ}		V _O = V _{CC} or GND	3.6 V			±10	μA
I _{CC}		V _I = V _{CC} or GND, I _O = 0	3.6 V			10	μA
ΔI _{CC}		One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μA
C _i	Control inputs	V _I = V _{CC} or GND	3.3 V			3.5	pF
	Data inputs					3.5	
C _O	Outputs	V _O = V _{CC} or GND	3.3 V			5.5	pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

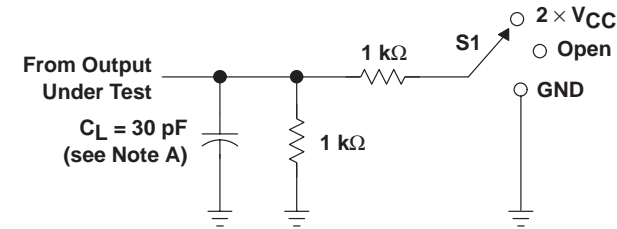
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	1.3	5.3	1	3.2	3.1		1.1	2.8	ns
t _{en}	\overline{OE}	Y	1.4	6.4	1	4.1	4.3		1	3.5	ns
t _{dis}	\overline{OE}	Y	1.8	5.9	1	3.4	4		1.4	4	ns

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT	
			TYP	TYP	TYP		
C _{pd}	Power dissipation capacitance per gate	Outputs enabled	C _L = 0, f = 10 MHz	15	17	19	pF
		Outputs disabled		2	2	3	



PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

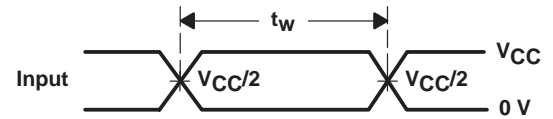


LOAD CIRCUIT

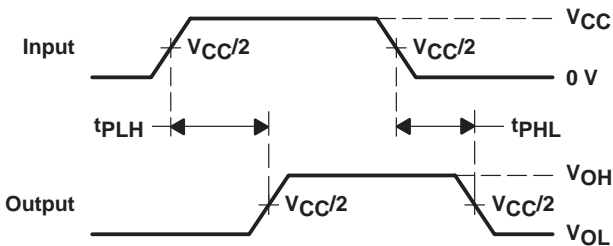
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 \times V_{CC}
t_{PHZ}/t_{PZH}	GND



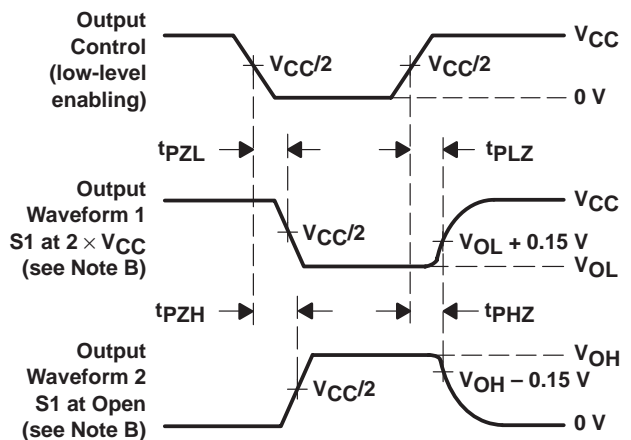
VOLTAGE WAVEFORMS
 SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
 PULSE DURATION



VOLTAGE WAVEFORMS
 PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
 ENABLE AND DISABLE TIMES

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

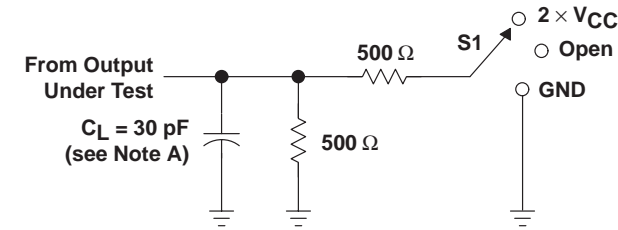
Figure 1. Load Circuit and Voltage Waveforms

SN74ALVC125
QUADRUPLE BUS BUFFER GATE
WITH 3-STATE OUTPUTS

SCES110D – JULY 1997 – REVISED DECEMBER 1998

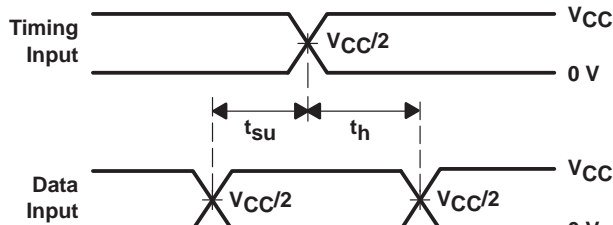
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5 V \pm 0.2 V$

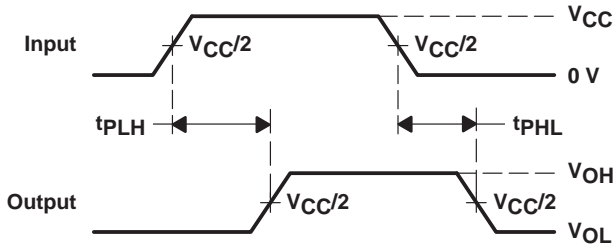


LOAD CIRCUIT

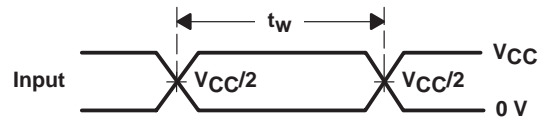
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND



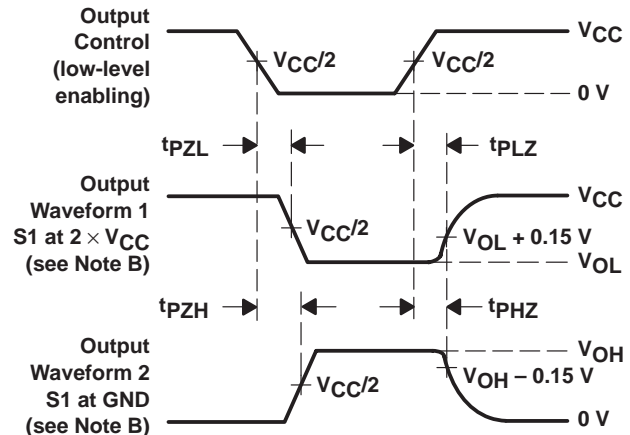
**VOLTAGE WAVEFORMS
 SETUP AND HOLD TIMES**



**VOLTAGE WAVEFORMS
 PROPAGATION DELAY TIMES**



**VOLTAGE WAVEFORMS
 PULSE DURATION**

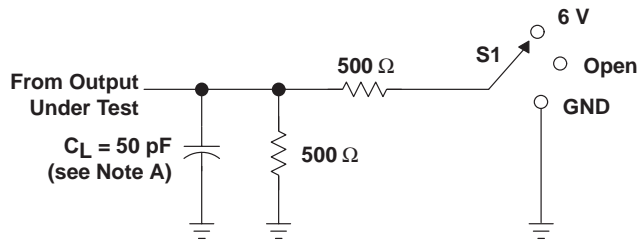


**VOLTAGE WAVEFORMS
 ENABLE AND DISABLE TIMES**

- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

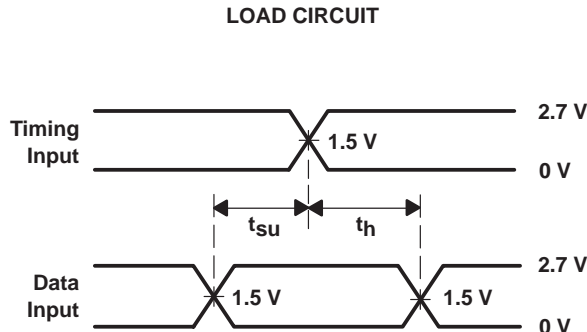
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 2.7\text{ V AND } 3.3\text{ V} \pm 0.3\text{ V}$

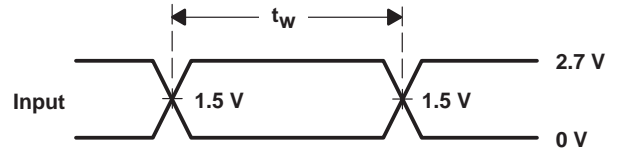


LOAD CIRCUIT

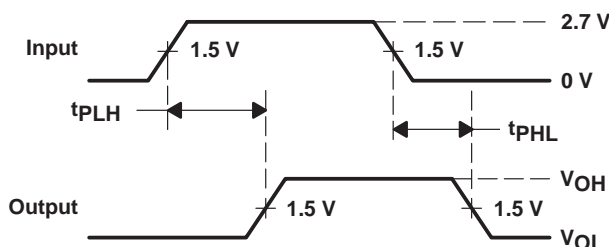
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



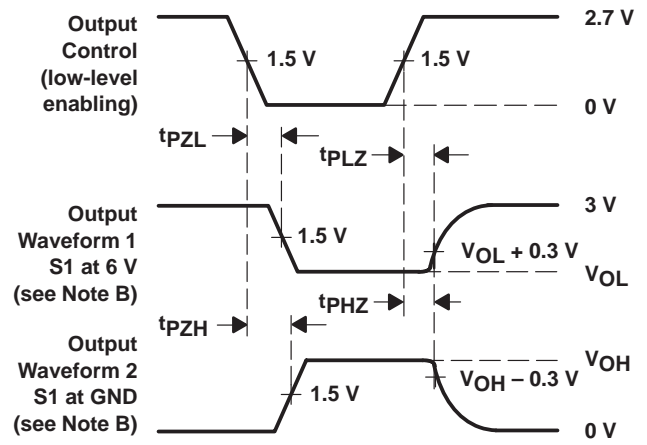
**VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES**



**VOLTAGE WAVEFORMS
PULSE DURATION**



**VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES**



**VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES**

- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.